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TC 3700 Inventor Search Program

See attached inventor searches for applications and/or patents to help resolve questions of overlapping subject matter. These searches are provided as an initial examination aid: examiners should perform updated or expanded PALM or EAST inventors searches as appropriate.

Serial Number: 16621 752

1.) See <u>attached</u> printout of inventors listed in PALM

2.) See <u>attached</u> EAST Inventor Search Printout shows Inventor search terms

TTO.	0000000		057/005	T	
US	20060223	Structure for	257/295		Moore;
20060038212		amorphous carbon			John et al.
A1		based non-volatile			
		memory			
US	20060216	Index extraction from	707/200		Simske;
20060036649		documents			Steven J. et
A1					al.
US	20060216	Index extraction from	707/100		Simske;
20060036614		documents			Steven J. et
A1					al.
US	20060216	Index extraction from	707/1		Simske;
20060036566	20000210	documents	'0'''		Steven J. et
A1		documents			al.
US	20060216	Transistor with	257/213		Moore;
20060033125	20000210		2377213		John T.
		nitrogen-hardened			Join 1.
A1	20060216	gate oxide	5/620	<u> </u>	1
US	20060216	Support device for	5/630		Moore;
20060031992		positioning a patient			John
A1		in a prone position		ļ	
US	20060209	Computerized	705/2	382/128	Serrano;
20060031093		method and system			Laura
A1		for communicating			Kathleen et
		agreements and/or			al.
		discrepancies in		·	
		image interpretation	l		
US	20060202	Products with data-	430/311		Gonzalez;
20060024617		encoding pattern			Manuel et
A1					al.
US	20060202	Front-end processing	257/786		Moore;
20060022352		of nickel plated bond			John et al.
Al		pads			
US	20060119		600/509	-	Blakley;
20060015033	20000117	characterization and	000/307		Daniel R. et
A1		compensation			al.
US	20060119	Use of dilute steam	257/315	365/185.01	Weimer;
1	20000119	ambient for	2311313	303/103.01	Ronald A.
20060011969					et al.
A1		improvement of flash	,		et ai.
110	20060112	devices	420/626		137-:
US	20060112	Anti-reflective	438/636		Weimer;
20060009028		coating doped with			Ronald A.
A1		carbon for use in			et al.
		integrated circuit			
		technology and			
		method of formation			
US	20060112	Semiconductor	438/287	438/775;	Beaman;
20060008998		assemblies, methods		438/786	Kevin L. et

				I	т.
Al		of forming structures			al.
		over semiconductor			
		substrates, and			
		methods of forming			
		transistors associated			
		with semiconductor			
		substrates			
US	20060112	Memory device,	257/204	257/536	Moore;
20060006421	20000112	programmable	237720.	2577550	John T. et
A1		resistance memory			al.
AI					αι.
		cell and memory			
TIO	20060112	array	2/150		Magnet
US	20060112	Human motor control	2/159		Moore;
20060005296		device and methods			John
Al					
US	20060105	Image reproduction	347/19		Martinez;
20060001690					Oscar et al.
A1					
US	20060105	Forecast weather	345/473	345/629	Johnson;
20060001668		video presentation			Chad W. et
A1		system and method			al.
US	20051208	Coatings for glass	65/374.11	65/374.12;	Moore,
20050268662		molding dies and		65/374.13	John J. et al.
A1		forming tools			
US	20051201	Method and	707/200		Moore,
20050267914		apparatus for			John Walter
Al		updating a database			et al.
1		using table staging		Ì	
		and queued			:
		relocation and			
		deletion			
US	20051201	Graded GexSe100-x	438/238		Moore,
20050266635	20031201	concentration in	150/250		John T. et
		PCRAM			al.
US US	20051201	Functionally graded	164/312	164/138	Moore,
1	20031201	alumina-based thin	107/312	107/130	John J. et al.
20050263261					Joint J. et al.
Al	20051124	film systems	524/00	106/400	Von
US	20051124	Color-converting	524/99	106/499;	Yang,
20050261400		photoluminescent		252/301.16;	Maizhi et
A1	0007177	film	505:1	252/301.35	al.
US	20051027	System and method	705/1		Lin,
20050240424		for hierarchical			Xiaofan et
A1		attribute extraction			al.
		within a call handling			
		system			
US	20051027	Method and system	704/246		Simske,

20050240407		for progenting content			Steven John
A1		for presenting content to an audience			et al.
US	20051013		704/256		Wilson,
20050228668	20031013	System and method for automatic	704/230		James M. et
l .				•	al.
A1		generation of dialog			ai.
TIC	20050022	run time systems	420/427	420/424	Mann
US	20050922	Methods of forming	438/437	438/424	Moore,
20050208730		materials within			John T. et
A1		openings, and			al.
		methods of forming			
	20050015	isolation regions	265/162		24
US	20050915	Method of refreshing	365/163		Moore,
20050201146		a PCRAM memory			John T. et
Al	20070001	device	510/100		al.
US	20050901	Dissolving gel for	510/188		Esposito,
20050192194		cured polysulfide			James R. et
A1		resins	0.511050		al.
US	20050818	Skewed sense AMP	365/185.2		Hush, Glen
20050180208		for variable resistance			et al.
A1		memory sensing		-010	· ·
US	20050811	Merit-based software	705/1	705/8	Lin,
20050177383		licensing			Xiaofan et
A1					al.
US	20050811	Automated speech	704/270.1		Yacoub,
20050177371		recognition			Sherif et al.
A1				· · · · · · · · · · · · · · · · · · ·	
US	20050811	System and method	379/265.13		Yacoub,
20050175167		for prioritizing			Sherif et al.
A1		contacts			
US	20050804	System and method	705/1		Lin,
20050171792		for language			Xiaofan et
Al		variation guided			al.
		operator selection			
US	20050804	System and method	379/88.16	379/88.02	Yacoub,
20050169441		for extracting			Sherif et al.
A1		demographic			
		information			
US	20050804	Capacitors, methods	257/310	257/640;	Moore,
20050167727		of forming		257/E21.008;	John T. et
A1		capacitors, and		257/E21.268;	al.
		methods of forming		438/250;	
		capacitor dielectric		438/761	
		layers			
US	20050804	Non-volatile zero	257/100		Campbell,
20050167689	1	field splitting			Kristy A. et
Al	<u> </u>	resonance memory	<u> </u>		al.

US 20050165796 A1	20050728	Method and system for managing image files in a hierarchical storage mangement	707/100		Moore, John A.
US 20050157844 A1	20050721	system Traveling X-ray inspection system with collimators	378/57		Bernardi, Richard T. et al.
US 20050157573 A1	20050721	Method of forming non-volatile resistance variable devices	365/200		Campbell, Kristy A. et al.
US 20050154531 A1	20050714	System and method for providing personalized weather reports and the like	702/3		Kelly, Terence F. et al.
US 20050151786 A1	20050714	Drop generating apparatus	347/42		Brookfield, John M. et al.
US 20050151783 A1	20050714	Drop generating apparatus	347/40		Brookfield, John M. et al.
US 20050150594 A1	20050714	Layered support and method for laminating CMP pads	156/307.7	156/289; 156/580	Kodaka, Ichiro et al.
US 20050148150 A1	20050707	Memory element and its method of formation	438/381	438/382	Moore, John T. et al.
US 20050146958 A1	20050707	Rewrite prevention in a variable resistance memory	365/203		Moore, John et al.
US 20050142289 A1	20050630	Polysulfide thermal vapour source for thin sulfide film deposition	427/248.1	204/192.1	Robert Stiles, James Alexander et al.
US 20050137103 A1	20050623	Stripper for cured negative-tone isoprene-based photoresist and bisbenzocyclobutene coatings	510/175	134/34; 510/407	Moore, John C.
US 20050136596 A1	20050623	Semiconductor constructions	438/261	257/E21.269; 257/E21.625	Moore, John T.
US	20050623	Chalcogenide glass	257/4	257/5;	Campbell,

20050133778		constant current		438/900	Kristy A. et
A1		device, and its		436/300	al.
***		method of fabrication			
		and operation			
US	20050609	Electrode structures	438/654		Brooks,
20050124155		and method to form			Joseph F. et
A1		electrode structures			al.
		that minimize			
		electrode work			
		function variation			
US	20050609	Memory architecture	365/63		Moore,
20050122757		and method of			John T. et
A1		manufacture and			al.
		operation thereof	206/25		7.4
US	20050602	Vehicle equipment	296/37.8		Moore,
20050116489		console			John A.
US	20050519	Remote mail	709/217		Hyder,
20050108359	20030319	management system	103/217		Robert et al.
A1		management system			Trobbit of all
US	20050519	Email application	709/206	715/727	Simske,
20050108338	20030313	with user voice			Steven J. et
A1		interface			al.
US	20050519	Compositions and	435/7.2	514/567	Maglich,
20050106635		methods for			Jodi Marie
A1		regulating thyroid			et al.
		hormone metabolism			
		and cholesterol and			
		lipid metabolism via			
		the nuclear receptor			
US	20050519	car Method for	427/421.1	427/8	Moore,
20050106328	20030319	predicting and	42//421.1	42//6	John R. et
A1		applying painting			al.
		parameters and use			<u></u>
		thereof			
US	20050505	Navigation routing	701/202	340/995.19;	Simske,
20050096840		system and method		701/209	Steven J.
Al					
US	20050428	Human	424/188.1	530/395	Moore,
20050089526		immunodeficiency			John P. et
A1		virus envelope			al.
		clycoprotein mutants			
		and uses thereof	0.00/0.00		1
US	20050421	Work piece holding	269/266		Moore,
20050082731		arrangement			John et al.

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Al					
US 20050079241 A1	20050414	Method and apparatus for molding composite articles	425/388	425/147	Moore, John et al.
US 20050076295 A1	20050407	System and method of specifying image document layout definition	715/517		Simske, Steven J. et al.
US 20050073732 A1	20050407	Systems and methods for scanning media	358/527	358/1.2; 358/474	Benedicto, Jordi Arnabat et al.
US 20050073719 A1	20050407	Color image processor	358/1.18	358/1.2	Amela, Eduardo et al.
US 20050065789 A1	20050324	System and method with automated speech recognition engines	704/231		Yacoub, Sherif et al.
US 20050061552 A1	20050324	Rotary drill bit	175/385	175/403	Moore, John F.
US 20050054207 A1	20050310	Plasma etching methods and methods of forming memory devices comprising a chalcogenide comprising layer received operably proximate conductive electrodes	438/710	257/E21.241; 257/E21.268	Li, Li et al.
US 20050019699 A1	20050127	Non-volatile resistance variable device	430/311	257/E29.101; 257/E29.17; 257/E45.002	Moore, John T.
US 20050009366 A1	20050113	Adhesive support method for wafer coating, thinning and backside processing	438/782		Moore, John C.
US 20050007852 A1	20050113	Method of refreshing a PCRAM memory device	365/222		Moore, John T. et al.
US 20040264234 A1	20041230	PCRAM cell operation method to control on/off resistance variation	365/148		Moore, John T. et al.

US 20040263908 A1	20041230	Raster image path architecture	358/2.1	358/3.21; 382/173	Jacobs, William S. et al.
US 20040251299 A1	20041216	Secure window mailer and method of making	229/92.3		Moore, John A.
US 20040241759 A1	20041202	High throughput screening of libraries	435/7.2		Tozer, Eileen et al.
US 20040238958 A1	20041202	Electrode structure for use in an integrated circuit	257/751	257/E21.582; 257/E23.02; 257/E27.004; 257/E45.002	Moore, John T. et al.
US 20040238918 A1	20041202	Method of manufacture of a PCRAM memory cell	257/528	257/536; 438/238; 438/382	Moore, John T. et al.
US 20040236566 A1	20041125	System and method for identifying special word usage in a document	704/4		Simske, Steven J.
US 20040233728 A1	20041125	Chalcogenide glass constant current device, and its method of fabrication and operation	365/185.24		Campbell, Kristy A. et al.
US 20040232551 A1	20041125	Electrode structure for use in an integrated circuit	257/753	257/758; 257/E21.582; 257/E23.02; 257/E27.004; 257/E45.002; 438/622; 438/644	Moore, John T. et al.
US 20040229423 A1	20041118	Electrode structure for use in an integrated circuit	438/222	257/E21.582; 257/E23.02; 257/E27.004; 257/E45.002	Moore, John T. et al.
US 20040225531 A1	20041111	Computerized system and method for automated correlation of mammography report with pathology specimen result	705/2	378/37	Serrano, Laura Kathleen et al.
US 20040224308 A1	20041111	Stabilized viral envelope proteins and uses thereof	435/5	435/235.1; 435/366; 435/456; 435/69.3;	Binley, James M. et al.

				530/350;	
	2001111	a:	067/000	536/23.72	
US	20041111	Skewed sense AMP	365/208	365/190;	Hush, Glen
20040223393		for variable resistance		365/207	et al.
Al		memory sensing			
US	20041111	Resistance variable	365/202		Campbell,
20040223390		memory element			Kristy A. et
A1		having chalcogenide			al.
		glass for improved			
		switching			
		characteristics			
US	20041111	Global column select	257/202		Moore,
20040222441		structure for			John T.
A1		accessing a memory			
US	20041028	Method and	257/42		Moore,
20040211957		apparatus for			John T. et
A1		controlling metal			al.
* * *		doping of a			
		chalcogenide			
		memory element			
US	20040930	Layered resistance	438/382		Campbell,
20040192006	20040930	variable memory	430/302		Kristy A. et
		device and method of			al.
A1	·				a1.
TIO	20040020	fabrication	438/123	257/E45.002	Campbell,
US	20040930	Method of forming	438/123	237/E43.002	Kristy A. et
20040191961		non-volatile			al.
A1		resistance variable			ai.
		devices and method			
		of forming a			
ļ		programmable			
		memory cell of			
		memory circuitry		4.5.6.000	
US	20040923	Textiles with high	442/79	156/279;	Moore,
20040185728		water release rates		442/108;	John W. et
A1		and methods for		442/173;	al.
		making same		442/174;	
				442/93	
US	20040923	Graded GexSe100-x	438/275	257/E45.002	Moore,
20040185625		concentration in			John T. et
A1		PCRAM			al.
US	20040923	Plasma nitridization	257/411	257/E21.193	Beaman,
20040183144		for adjusting			Kevin L. et
A1	1	transistor threshold			al.
		voltage			
	l .				
US	20040923	Gated semiconductor	257/315	257/324;	Helm, Mark

A1		methods of forming gated semiconductor assemblies		257/E29.302; 438/211; 438/216	
US 20040179390 A1	20040916	CHALCOGENIDE GLASS CONSTANT CURRENT DEVICE, AND ITS METHOD OF FABRICATION AND OPERATION	365/148		Campbell, Kristy A. et al.
US 20040178669 A1	20040916	Glide mount support base apparatus for child restraint car safety seat	297/250.1		Lady, Suzanne D. et al.
US 20040175859 A1	20040909	Single polarity programming of a PCRAM structure	438/102		Campbell, Kristy A. e al.
US 20040174900 A1	20040909	Method and system for providing broadband multimedia services	370/466	370/432	Volpi, John P. et al.
US 20040174443 A1	20040909	System and method for storing of records in a database	348/231.3	348/231.2	Simske, Steven J.
US 20040173861 A1	20040909	Transistor with nitrogen-hardened gate oxide	257/411	257/E21.193	Moore, John T.
US 20040171811 A1	20040902	Nonhuman pregnane x receptor sequences for use in comparative pharmacology	530/358	435/320.1; 435/325; 435/6; 435/69.1; 536/23.5	Kliewer, Steven Anthony et al.
US 20040171209 A1	20040902	Novel masked nitrogen enhanced gate oxide	438/239	257/E21.625	Moore, John T. et al.
US 20040171018 A1	20040902	Mouse farnesoid x receptor sequences for use in comparative pharmacology	435/6	435/320.1; 435/325; 435/69.1; 530/350; 536/23.5	Holt, Jasor A. et al.
US 20040169387 A1	20040902	Vehicle equipment console	296/24.34		Moore, John A.
US 20040164336 A1	20040826	Films doped with carbon for use in integrated circuit	257/296	257/E21.274	Weimer, Ronald A. et al.

		technology			
US 20040164335 A1	20040826	Double sided container process used during the manufacture of a semiconductor device	257/296	257/E21.019; 257/E21.658	DeBoer, Scott J. et al.
US 20040161874 A1	20040819	Method of forming a non-volatile resistance variable device, and non- volatile resistance variable device	438/102	257/E27.071; 257/E45.002	Moore, John T. et al.
US 20040158820 A1	20040812	System for generating an application framework and components	717/136	717/101	Moore, John Wesley et al.
US 20040157417 A1	20040812	Methods to form a memory cell with metal-rich metal chalcogenide	438/510	257/E27.004; 257/E45.002; 438/128; 438/238	Moore, John T. et al.
US 20040157416 A1	20040812	Method of forming a non-volatile resistance variable device, and non-volatile resistance variable device	438/501	257/E21.006; 257/E27.071; 257/E45.002	Moore, John T. et al.
US 20040147069 A1	20040729	Semiconductor assemblies, methods of forming structures over semiconductor substrates, and methods of forming transistors associated with semiconductor substrates	438/197	438/287	Beaman, Kevin L. et al.
US 20040146806 A1	20040729	Photo-imageable nanocomposites	430/287.1	430/284.1; 430/285.1; 430/286.1; 430/306	Roberts, David H. et al.
US 20040141584 A1	20040722	HIGH ENERGY X- RAY MOBILE CARGO INSPECTION SYSTEM WITH PENUMBRA	378/57		Bernardi, Richard T. et al.

		COLLIMATOR			
US 20040133560 A1	20040708	Methods and systems for organizing electronic documents	707/3		Simske, Steven J.
US 20040124441 A1	20040701	Semiconductor wafer assemblies comprising photoresist over silicon nitride materials	257/200	257/E21.257; 257/E21.259; 257/E21.293	Moore, John T. et al.
US 20040124406 A1	20040701	Method of forming non-volatile resistance variable devices, method of forming a programmable memory cell of memory circuitry, and a non-volatile resistance variable device	257/4	257/E45.002	Campbell, Kristy A. et al.
US 20040124268 A1	20040701	Spray gun with internal mixing structure	239/398		Frazier, Keith et al.
US 20040121618 A1	20040624	Spin-on adhesive for temporary wafer coating and mounting to support wafer thinning and backside processing	438/782		Moore, John C.
US 20040102046 A1	20040527	Semiconductor processing method using photoresist and an antireflective coating	438/689	257/E21.029; 257/E21.232; 257/E21.577	Gilton, Terry L. et al.
US 20040095560 A1	20040520	Correction optics for flat-panel displays	353/79		Travis, Adrian Robert Leigh et al.
US 20040094813 A1	20040520	Methods of forming dielectric materials and methods of processing semiconductor substrates	257/411	257/406; 257/E21.193; 257/E21.268; 257/E21.293; 257/E29.165	Moore, John T.
US	20040506	Uses of a chemokine	424/208.1	424/130.1;	Allaway,

20040006520				424/196 1.	Cualiana D
20040086528	1	receptor for		424/186.1;	Graham P.
A1		inhibiting HIV-1		424/204.1;	et al.
		infection		435/6;	
				435/91.1;	
				514/12	
US	20040422	Metal safe stabilized	134/2	134/26;	Moore,
20040074519		stripper for removing		510/176	John C.
A1		cured polymeric			
		layers and negative			
		tone acrylic			
		photoresists			
US	20040415	PCRAM rewrite	365/232		Moore,
20040071042		prevention			John et al.
A1					
US	20040401	System and method	707/5		Simske,
20040064447		for management of			Steven J. et
A1		synonymic searching			al.
US	20040401	Method and system	600/558		Zhou,
20040064064		for detecting the			Qienyuan et
A1		effects of alzheimer's			al.
		disease in the human			
		retina			
US	20040401	Semiconductor	365/201		Muller,
20040062104		handler interface auto			Luis A. et
A1		alignment			al.
US	20040318	Graded GexSe100-x	438/225	257/E45.002	Moore,
20040053461		concentration in			John T. et
A1		PCRAM			al.
US	20040318	Non-volatile	257/489	257/E29.101;	Moore,
20040051157		resistance variable		257/E29.17;	John T.
A1		device		257/E45.002	
US	20040311	System for and	715/512		Simske,
20040049734		method of generating			Steven J.
A1		image annotation			
		information			
US	20040304	METHODS TO	438/510	257/E27.004;	Moore,
20040043585		FORM A MEMORY		257/E45.002	John T. et
A1		CELL WITH			al.
		METAL-RICH			
		METAL			
		CHALCOGENIDE			
US	20040304	Method to control	428/644	257/644	Moore,
20040043245		silver concentration			John T. et
A1		in a resistance	1		al.
		variable memory			
		element	1		
					

US 20040042658 A1	20040304	Document analysis system and method	382/173		Simske, Steven J. et al.
US 20040042265 A1	20040304	Method and apparatus for controlling metal doping of a chalcogenide memory element	365/163		Moore, John T. et al.
US 20040042259 A1	20040304	Single polarity programming of a pcram structure	365/158	365/171; 365/173	Campbell, Kristy A. et al.
US 20040039466 A1	20040226	Method and apparatus for high speed data dumping and communication for a down hole tool	700/95		Lilly, Dave et al.
US 20040038480 A1	20040226	Method of manufacture of a PCRAM memory cell	438/257		Moore, John T. et al.
US 20040037470 A1	20040226	Systems and methods for processing text-based electronic documents	382/229		Simske, Steven J.
US 20040029351 A1	20040212	Methods of forming non-volatile resistance variable devices and methods of forming silver selenide comprising structures	438/382	257/E45.002	Gilton, Terry L. et al.
US 20040023457 A1	20040205	Global column select structure for accessing a memory	438/257		Moore, John T.
US 20040019385 A1	20040129	Manufacture of porous net-shaped materials comprising alpha or beta tricalcium phosphate or mixtures thereof	623/23.5		Ayers, Reed A. et al.
US 20040018560 A1	20040129	Crystallized LXR polypeptide in complex with a ligand and screening methods employing same	435/7.1	530/350; 702/19	Bledsoe, Randy K. et al.

US 20040017941 A1	20040129	System and method for bounding and classifying regions within a graphical image	382/180		Simske, Steven J.
US 20040015775 A1	20040122	Systems and methods for improved accuracy of extracted digital content	715/500		Simske, Steven J. et al.
US 20040013906 A1	20040122	Oxygen substituted barium thioaluminate phosphor materials	428/690	252/301.4S; 313/503; 313/509; 428/917	Stiles, James Alexander Robert et al.
US 20040013318 A1	20040122	System and method for manipulating a skewed digital image	382/289		Simske, Steven J. et al.
US 20040008884 A1	20040115	System and method for scanned image bleedthrough processing	382/165	382/170; 382/173	Simske, Steven John et al.
US 20040002851 A1	20040101	System and method of automatic personalization of computer users' computing experience	704/9		Simske, Steven J.
US 20030223637 A1	20031204	System and method of locating a non-textual region of an electronic document or image that matches a user-defined description of the region	382/176		Simske, Steve John et al.
US 20030222280 A1	20031204	Apparatus and method for dual cell common electrode PCRAM memory device	257/200		Moore, John
US 20030210249 A1	20031113	System and method of automatic data checking and correction	345/581		Simske, Steven J.
US 20030209778 A1	20031113	CAPACITORS	257/532	257/528; 257/E21.008; 257/E21.268	Moore, John T. et al.

US 20030207592 A1	20031106	Method of forming a capacitor dielectric layer	438/775	257/E21.008; 257/E21.268; 438/776; 438/777	Moore, John T. et al.
US 20030206182 A1	20031106	Synchronized graphical information and time-lapse photography for weather presentations and the like	345/632		Kelly, Terence F. et al.
US 20030187617 A1	20031002	User perception tool	702/186		Murphy, Stephen F. et al.
US 20030185036 A1	20031002	Method for programming a memory cell	365/100		Gilton, Terry L. et al.
US 20030175622 A1	20030918	High performance, photoimageable resin compositions and printing plates prepared therefrom	430/285.1	430/281.1; 430/283.1; 430/284.1; 430/286.1; 430/287.1; 430/306; 522/100; 522/102; 522/103; 522/110; 522/95	Hu, Yuxin et al.
US 20030169625 A1	20030911	Programmable conductor random access memory and method for sensing same	365/189.07		Hush, Glen et al.
US 20030160242 A1	20030828	DRAM cell constructions	257/68	257/E21.65	Gonzalez, Fernando et al.
US 20030156468 A1	20030821	Resistance variable 'on' memory	365/200	257/E45.002	Campbell, Kristy A. et al.
US 20030155606 A1	20030821	Method to alter chalcogenide glass for improved switching characteristics	257/314		Campbell, Kristy A. et al.
US 20030155589 A1	20030821	Silver- selenide/chalcogenide glass stack for	257/225		Campbell, Kristy A. et al.

-		resistance variable			
US 20030154321 A1	20030814	Method and system for registering a control within an operating environment using a control manager	719/320		Wyke, Kenneth C. et al.
US 20030153190 A1	20030814	Semiconductor processing method using photoresist and an antireflective coating	438/694	257/E21.029; 257/E21.232; 257/E21.577	Gilton, Terry L. et al.
US 20030153166 A1	20030814	Transistor and method of making the same	438/484	257/E21.193	Moore, John T.
US 20030148904 A1	20030807	Cured polymers dissolving compositions	510/201	134/26; 134/4; 257/E21.255; 510/219	Moore, John C.
US 20030143782 A1	20030731	METHODS OF FORMING GERMANIUM SELENIDE COMPRISING DEVICES AND METHODS OF FORMING SILVER SELENIDE COMPRISING STRUCTURES	438/128	257/E45.002	Gilton, Terry L. et al.
US 20030128612 A1	20030710	PCRAM rewrite prevention	365/222	365/149; 365/150	Moore, John et al.
US 20030125594 A1	20030703	Catalyst formulation comprising ceramic foam material	585/520	422/131; 422/211; 502/178; 502/412; 585/510	Moore, John H.
US 20030120698 A1	20030626	Manager for software controls in an operating environment	718/100		Wyke, Kenneth C. et al.
US 20030120697 A1	20030626	System and method for adapting a software control in an	718/100		Wyke, Kenneth C. et al.

		operating			
		environment			
US 20030119563 A1	20030626	Electronic interactive communication system and the method therefor	455/566		Wyke, Kenneth C. et al.
US 20030117438 A1	20030626	System and method for manipulating data using a control	715/764		Wyke, Kenneth C. et al.
US 20030096497 A1	20030522	Electrode structure for use in an integrated circuit	438/652	257/E21.582; 257/E23.02; 257/E27.004; 257/E45.002; 438/658; 438/660; 438/666	Moore, John T. et al.
US 20030085436 A1	20030508	Method of forming low dielectric silicon oxynitride spacer films highly selective to etchants	257/408	257/E21.268; 257/E21.269; 257/E21.507; 438/303; 438/595	Moore, John T.
US 20030084824 A1	20030508	Process for producing building materials from raw paint sludge	106/739	106/277	Matheson, Robert R. et al.
US 20030074081 A1	20030417	Non-uniform porosity tissue implant	623/23.5	623/23.76	Ayers, Reed A.
US 20030068855 A1	20030410	Method for forming protective films and spacers	438/216	257/E21.507	Moore, John T.
US 20030067183 A1	20030410	Vehicle equipment console	296/24.34		Moore, John A.
US 20030063703 A1	20030403	Computed tomography with virtual tilt and angulation	378/17	378/15	Moore, John F.
US 20030061832 A1	20030403	Combustion synthesis of glass (Al2O3-CaO-X-Y) ceramic (TiB2) composites	65/17.4		Yi, Hu Chun et al.
US 20030057514 A1	20030327	INTEGRATED CIRCUIT FORMED BY REMOVING UNDESRABLE SECOND OXIDE	257/507	257/E21.251; 257/E21.268; 257/E21.552	Chapek, David L. et al.

				,	
		WHILE	:		
		MINIMALLY			
·		AFFECTING A			
		DESIRABLE FIRST			
		OXIDE			
US	20030320	Stabilized viral	345/41		Binley,
20030052839		envelope proteins and			James M. et
A1		uses thereof			al.
US	20030313	System and method	702/3		Moore,
20030050757		for processing			John S.
A1		weather information			
US	20030313	METHOD OF	438/385	257/E45.002;	Campbell,
20030049912		FORMING		365/225.7;	Kristy A. et
A1		CHALCOGENIDE		438/102;	al.
		COMPRSING		438/131	
		DEVICES AND			
		METHOD OF			
		FORMING A			
		PROGRAMMABLE			
		MEMORY CELL OF			
		MEMORY			
		CIRCUITRY			
US	20030306	Multi-media	725/133	725/110	Moore,
20030046710		communication			John F.
Al		system for the			
		disabled and others			
US	20030306	Method of forming	438/257	257/E45.002;	Campbell,
20030045054		non-volatile		365/182	Kristy A. et
Al		resistance variable			al.
		devices, method of			
		forming a			
		programmable			
		memory cell of			
		memory circuitry,			
		and a non-volatile			
		resistance variable			
		device			
US	20030306	Capacitors, methods	438/239	257/296;	Moore,
20030045050		of forming		257/E21.008;	John T. et
A1		capacitors, and		257/E21.268;	al.
		methods of forming		438/381	
		capacitor dielectric			
		layers			
US	20030306	Method of forming	438/237		Campbell,
20030045049		chalcogenide		1	Kristy A. et
Al		comprising devices			al.
	l		<u> </u>	I	1

US	20030227	Annaratus and	257/200		Moore,
	20030227	Apparatus and	2377200		John
20030038301		method for dual cell			JOIN
A1		common electrode			
		PCRAM memory			
		device			
US	20030206	METHOD OF	438/618	257/E21.582;	Moore,
20030027416		FORMING		257/E21.645;	John T.
A1		INTEGRATED		257/E27.081	ì
		CIRCUITRY,	!		
		METHOD OF			
		FORMING			
		MEMORY	ì		
		CIRCUITRY, AND			
		METHOD OF			
		FORMING			
		RANDOM ACCESS			
		MEMORY			
		CIRCUITRY			
US	20030130	Films doped with	257/296	257/E21.274	Weimer,
20030020108	20030130	carbon for use in	2511270	2377221.27	Ronald A.
A1		integrated circuit			et al.
AI		technology		,	
TIC	20030102		438/253	257/E21.65	Gonzalez,
US	20030102	Methods of forming DRAM cells	430/233	257/E21.05	Fernando et
20030003655		DRAM cells			al.
A1	20020102	C1 1 '1	257/520	257/526	
US	20030102	Chalcogenide	257/528	257/536;	Moore,
20030001229		comprising device		257/E27.071;	John T. et
A1				257/E45.002;	al.
				438/381;	
				438/510;	
				438/518;	
				438/535	
US	20021226	System and method	358/474	358/527	Simske,
20020196479		of automated scan			Steven J.
Al		workflow assignment			
US	20021205	Transistor structures,	438/287	257/E21.193;	Sandhu,
20020182812		methods of		257/E29.162	Gurtej S. et
A1		incorporating			al.
		nitrogen into silicon-			
		oxide-containing			
	1	layers; and methods	1		
		of forming transistors			
US	20021205	Novel masked	438/287	257/E21.625;	Moore,
20020182811		nitrogen enhanced		438/770	John T. et
A1		gate oxide			al.
US	20021121	High performance,	430/18	430/284.1;	Hu, Yuxin
	20021121	ingii perioritance,	130/10	1.50/201.15	1 - 1 40, 1 4/1111

20020172875		photoimageable resin		522/95	et al.
A1		compositions and			
		printing plates			
		prepared therefrom			
US	20021114	Double sided	438/396	257/E21.019;	DeBoer,
20020168830		container process		257/E21.658;	Scott J. et
A1		used during the		438/253	al.
		manufacture of a			
		semiconductor device			
US	20021017	Semiconductor	438/791	257/E21.206;	DeBoer,
20020151191		processing methods		257/E21.269	Scott
A1		of transferring			Jeffrey et al.
		patterns from			
		patterned Photoresists			
		to materials, and			
		structures comprising			
TIC	20021017	silicon nitride	438/703	257/E21 206	DeBoer,
US 20020151180	20021017	Semiconductor	438//03	257/E21.206; 257/E21.269;	Scott
A1		processing methods of transferring		438/791	Jeffrey et al.
AI		patterns from		430/731	Jerney et al.
		patterned photoresists]
		to materials, and			
		structures comprising			
		silicon nitride			
US	20021017	Semiconductor	438/585	257/E21.206;	DeBoer,
20020151160		processing methods		257/E21.269;	Scott
A1		of transferring		438/744	Jeffrey et al.
		patterns from			
}		patterned photoresists			
	1	to materials, and			
		structures comprising			
		silicon nitride			
US	20021010	Semiconductor	438/724	257/E21.206;	DeBoer,
20020146910		processing methods		257/E21.269;	Scott
A1		of transferring		438/791	Jeffrey et al.
		patterns from			
	(patterned photoresists			
		to materials, and			
		structures comprising silicon nitride			
US	20021010	Layered image	345/629		Moore,
20020145615	20021010	rendering	343/029		John S.
A1		Tendering			Joini S.
US	20020919	Methods of forming	438/692	257/E21.244;	Moore,
20020132483	20020717	materials within	130,072	257/E21.55	John T. et
20020132703	<u> </u>	materials within	L	2377221.33	1.00

Al		openings, and			al.
		methods of forming isolation regions			
US 20020127886 A1	20020912	Method to manufacture a buried electrode PCRAM cell	438/800	257/E45.002	Moore, John T. et al.
US 20020123248 A1	20020905	METHODS OF METAL DOPING A CHALCOGENIDE MATERIAL	438/795	257/E21.006; 257/E27.071; 257/E45.002	Moore, John T. et al.
US 20020123170 A1	20020905	PCRAM cell manufacturing	438/102	257/E45.002; 438/103	Moore, John T. et al.
US 20020123169 A1	20020905	Methods of forming non-volatile resistance variable devices, and non- volatile resistance variable devices	438/95	257/E21.006; 257/E27.071; 257/E45.002	Moore, John T. et al.
US 20020117709 A1	20020829	Use of dilute steam ambient for improvement of flash devices	257/315	257/E21.209; 257/E29.165	Weimer, Ronald A. et al.
US 20020113979 A1	20020822	System and method for scan-to-print architecture	358/1.6	358/1.15	Rahgozar, M. Armoh et al.
US 20020111039 A1	20020815	Method of forming low dielectric silicon oxynitride spacer films highly selective to etchants	438/778	257/499; 257/506; 257/E21.268; 257/E21.269; 257/E21.507; 438/791; 438/794	Moore, John T.
US 20020109870 A1	20020815	System and method for scan-to- print architecture	358/504	358/531	Moore, John A. et al.
US 20020109199 A1	20020815	Transistor devices	257/411	257/406; 257/410; 257/E21.193; 257/E21.268; 257/E21.293; 257/E29.165	Moore, John T.
US 20020106896 A1	20020808	Batch processing for semiconductor wafers to form aluminum	438/688	257/E21.029; 257/E21.035; 257/E21.168;	Kraus, Brenda D. et al.

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		nitride and titanium		257/E21.17;	
		aluminum nitride		257/E21.292;	
				257/E21.576	
US	20020808	Method of forming	438/213	257/E29.101;	Moore,
20020106849		non-volatile		257/E29.17;	John T.
A1		resistance variable		257/E45.002	
		devices, method of			
		precluding diffusion			
		of a metal into			
		adjacent			
		chalcogenide			
		material, and non-			
		volatile resistance			
		variable devices			
US	20020725	Methods Of Forming	438/732	257/E21.193;	Sandhu,
20020098710		Transistors		257/E29.162	Gurtej S. et
A1					al.
US	20020718	Methods of forming a	438/197	257/E21.193;	Sandhu,
20020094621		nitrogen enriched		257/E29.162	Gurtej S. et
A1		region			al.
US	20020718	Transistor Structures	438/197	257/E21.193;	Sandhu,
20020094620	20020710		150,15,	257/E29.162	Gurtej S. et
A1				23771323.102	al.
US	20020620	Semiconductor	257/213		Beaman,
	20020020		2311213		Kevin L. et
20020074576		assemblies, methods			al.
A1		of forming structures			ai.
		over semiconductor			
		substrates, and			
		methods of forming			
		transistors associated			
		with semiconductor			
		substrates			
US	20020606	Goal-orinted design	715/776		Moore,
20020067375		for the printer			John
Al		proprety's graphical			Anthony et
		user interface			al.
US	20020523	Non-uniform porosity	623/23.76	623/16.11	Ayers, Reed
20020062154		tissue implant			A.
A1					
US	20020523	Transistor and	438/268	257/E21.193	Moore,
20020061624	20020323	method of making the	150/200	23.7.1.21.173	John T.
		_			JOILL T.
		same			ļ
Al	20020500	DD AM coll	120/252	1 257/E21 65	Gonzolez
US	20020509	DRAM cell	438/253	257/E21.65	Gonzalez,
US 20020055225	20020509	DRAM cell constructions	438/253	257/E21.65	Fernando et
US	20020509		438/253 257/325	257/E21.65 257/E21.193	

20020053693 A1		method of making the			John T.
US 20020047202 A1	20020425	Semiconductor wafer assemblies comprising photoresist over silicon nitride materials	257/751	257/E21.257; 257/E21.259; 257/E21.293	Moore, John T. et al.
US 20020047142 A1	20020425	STRUCTURES COMPRISING SILICON NITRIDE	257/288	257/E21.206; 257/E21.269 CIPG 20060101 A H01L H01L21/02 F I R US M 20060101 CIPC H01L CIPP H01L21/02 20060101 CIPG 20060101 A H01L H01L21/28 L I R US M 20060101 CIPC H01L CIPS H01L21/28 20060101	DeBoer, Scott Jeffrey et al.
US 20020032114 A1	20020314	Combustion synthesis of glass (Al2O3-B2-O3-MgO) ceramic (Tib2) composites	501/32	501/10; 501/39	Yi, Hu Chun et al.
US 20020019622 A1	20020214	CONTAINER CAP ASSEMBLY HAVING AN ENCLOSED PENETRATOR	604/411	141/329; 215/247; 604/415	DAUBERT RICHARD F. et al.
US 20020019142 A1	20020214	Methods of forming transistors associated with semiconductor substrates	438/765	257/E21.269; 257/E21.625	Moore, John T.
US 20020006736 A1	20020117	Methods of forming transistors associated with semiconductor	438/765	257/E21.269; 257/E21.625	Moore, John T.

		substrates			
US 20020001897 A1	20020103	METHODS OF FORMING GATED SEMICONDUCTOR ASSEMBLIES	438/201	257/E29.165; 257/E29.302	HELM, MARK A. et al.
US 20010049198 A1	20011206	Methods of forming materials within openings, and methods of forming isolation regions	438/689	257/E21.244; 257/E21.55	Moore, John T. et al.
US 20010044218 A1	20011122	SEMICONDUCTOR PROCESSING METHODS OF FORMING PHOTORESIST OVER SILICON NITRIDE MATERIALS	438/763	257/E21.257; 257/E21.259; 438/782; 438/791	MOORE, JOHN T. et al.
US 20010042884 A1	20011122	GATED SEMICONDUCTOR ASSEMBLIES	257/324	257/E29.165; 257/E29.302	HELM, MARK A. et al.
US 20010034129 A1	20011025	Capacitor constructions, DRAM constructions, semiconductive material assemblies, etching processes, and methods for forming capacitors and DRAMs	438/689	257/E21.008; 257/E21.27	Moore, John T. et al.
US 20010017401 A1	20010830	Method and apparatus for endpointing planarization of a microelectronic substrate	257/635	257/634; 257/915; 257/E21.244	Moore, John T.
US 20010014521 A1	20010816	Batch processing for semiconductor wafers to form aluminum nitride and titanium aluminum nitride	438/586	257/E21.029; 257/E21.035; 257/E21.168; 257/E21.17; 257/E21.292; 257/E21.576	Kraus, Brenda D. et al.
US 20010004543 A1	20010621	Semiconductor processing method and trench isolation	438/402	257/E21.318; 257/E21.546; 438/424;	Moore, John T.

		method		438/473	
US 20010001116 A1	20010510	Container cap assembly having an enclosed penetrator	604/200	215/296	Daubert, Richard F. et al.
US 20010000794 A1	20010503	Container cap assembly having an enclosed penetrator	604/200	222/80	Daubert, Richard F. et al.
US 20010000793 A1	20010503	Container cap assembly having an enclosed penetrator	604/200	222/80	Daubert, Richard F. et al.
US 7005409 B2	20060228	Dissolving gel for cured polysulfide resins	510/212	510/175; 510/201; 510/245; 510/254; 510/499; 510/500; 510/501	Esposito; James R. et al.
US 6998697 B2	20060214	Non-volatile resistance variable devices	257/529	257/136; 257/2; 257/296; 257/3; 257/4; 257/5; 257/508; 257/530; 257/537; 257/613; 257/614; 257/616; 257/78; 365/129; 365/148; 365/163; 365/171; 365/182; 438/257	Campbell; Kristy A. et al.
US 6988995 B2	20060124	Method and system for detecting the effects of Alzheimer's disease in the human retina	600/558	356/484	Zhou; Qienyuan et al.
US 6980332 B2	20051227	System and method of automated scan workflow assignment	358/445	358/446; 358/447; 358/461; 358/463; 358/475;	Simske; Steven J.

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				358/504;	
				358/509;	
				382/270;	
				382/273	
US 6969146	20051129	Drop generating	347/40	347/43;	Brookfield;
B2		apparatus		347/68	John M. et
					al.
US 6967383	20051122	Transistor with	257/410	257/411;	Moore;
B2	20001122	nitrogen-hardened	20 // 120	438/474;	John T.
		gate oxide		438/761;	John 1.
		gate oxide		438/763	
US 6963413	20051108	System and method	358/1.13	382/217;	Rahgozar;
	20031108		338/1.13	1	M. Armon
B2		for scan-to-print		715/505;	
		architecture		715/506;	et al.
				715/908	
US 6963101	20051108	Films doped with	257/306	257/296;	Weimer;
B2		carbon for use in		257/309	Ronald A.
		integrated circuit			et al.
		technology			
US 6961277	20051101	Method of refreshing	365/222	365/185.18;	Moore;
B2		a PCRAM memory		365/185.25;	John T. et
		device		365/226	al.
US 6961140	20051101	System and method	358/1.15	358/1.18;	Moore;
B2	20001101	for scan-to-print		358/1.6;	John A. et
B2		architecture		358/3.27;	al.
				358/406	
US 6961061	20051101	Forecast weather	345/473	345/634;	Johnson;
B1	20051101	video presentation	343/473	702/3	Chad W. et
DI		_		10213	al.
110 (055040	20051010	system and method	120/05	438/795	
US 6955940	20051018	Method of forming	438/95	438/793	Campbell;
B2		chalcogenide			Kristy A. et
		comprising devices		2.5.5.2.2	al.
US 6953720	20051011	Methods for forming	438/238	257/E45.002;	Moore;
B2		chalcogenide glass-		438/29;	John T. et
		based memory		438/381	al.
		elements			
US 6951805	20051004	Method of forming	438/618	257/E21.582;	Moore;
B2		integrated circuitry,		257/E21.645;	John T.
		method of forming		257/E27.081;	
		memory circuitry,		438/637;	
		and method of		438/667	
		forming random			
		access memory			
		circuitry			
US 6951791	20051004	Global column select	438/257	438/453	Moore;
B2	20031004	structure for	150/25/	150/455	John T.
D2	L	Structure 101	l	1	10ш1.

		accessing a memory			
US 6949789 B2	20050927	Use of dilute steam ambient for improvement of flash devices	257/315	257/321; 257/325; 257/E21.209; 257/E29.165	Weimer; Ronald A. et al.
US 6949402 B2	20050927	Method of forming a non-volatile resistance variable device	438/95	257/E27.071; 257/E45.002; 438/102	Moore; John T. et al.
US 6937528 B2	20050830	Variable resistance memory and method for sensing same	365/189.07	365/203	Hush; Glen et al.
US 6930909 B2	20050816	Memory device and methods of controlling resistance variation and resistance profile drift	365/148	365/158; 365/189.07	Moore; John T. et al.
US 6918391 B1	20050719	Multi-lumen endotracheal tube	128/842	128/207.14; 128/207.15; 128/911; 600/116; 600/120; 600/158	Moore; Johnny V.
US 6912147 B2	20050628	Chalcogenide glass constant current device, and its method of fabrication and operation	365/113	365/148; 365/163	Campbell; Kristy A. et al.
US 6909656 B2	20050621	PCRAM rewrite prevention	365/222	365/203	Moore; John et al.
US 6894304 B2	20050517	Apparatus and method for dual cell common electrode PCRAM memory device	257/4	257/2; 257/295; 257/3; 257/310; 257/5; 257/758	Moore; John
US 6891749 B2	20050510	Resistance variable 'on ' memory	365/163	257/2; 257/E45.002; 365/100; 365/113; 365/114; 365/148	Campbell; Kristy A. et al.
US 6891245 B2	20050510	Integrated circuit formed by removing undesirable second	257/506	257/510; 257/E21.251; 257/E21.268;	Chapek; David L. et al.

		oxide while		257/E21.552	
		minimally affecting a		20//221/002	
		desirable first oxide			
US 6891215	20050510	Capacitors	257/298	257/239;	Moore;
B2		F		257/299;	John T. et
				257/300;	al.
				257/301;	
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				257/311;	
				257/312;	
				257/313;	
				257/E21.008;	
				257/E21.268	
US 6890878	20050510	Catalyst formulation	502/439	428/312.2;	Moore;
B2	. ,	comprising ceramic		428/312.6;	John H.□
		foam material		428/313.3;	
				428/317.9;	
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				501/154;	
				501/80;	
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				502/214;	
				502/232;	
				502/412;	
				502/527.14;	
				502/527.16;	
				502/527.24	
US 6888771	20050503	Skewed sense AMP	365/208	365/190;	Hush; Glen
B2		for variable resistance		365/207	et al.
110 600 150 5	20050:05	memory sensing	120/602	057/201011	
US 6884725	20050426	Methods of forming	438/692	257/E21.244;	Moore;
B2		materials within		257/E21.55;	John T. et
		openings, and		438/700;	al.
		methods of forming		438/723;	
110 (000 550	20050412	isolation regions	265/100.01	438/724	24
US 6882578	20050419	PCRAM rewrite	365/189.01	365/203;	Moore;

B2		prevention		365/207	John et al.
US 6881623 B2	20050419	Method of forming chalcogenide comprising devices, method of forming a programmable memory cell of memory circuitry, and a chalcogenide comprising device	438/257	257/E45.002; 365/129; 365/132; 365/135; 365/140; 365/170; 365/180; 365/188	Campbell; Kristy A. et al.
US 6880122 B1	20050412	Segmenting a document into regions associated with a data type, and assigning pipelines to process such regions	715/500	382/176; 715/520; 715/521	Lee; Jeffrey P et al.
US 6878585 B2	20050412	Methods of forming capacitors	438/253	257/E21.008; 257/E21.268; 438/396; 438/703; 438/757; 438/761; 438/775; 438/791	Moore; John T. et al.
US 6875707 B2	20050405	Method of forming a capacitor dielectric layer	438/775	257/E21.008; 257/E21.268	Moore; John T. et al.
US 6869894 B2	20050322	Spin-on adhesive for temporary wafer coating and mounting to support wafer thinning and backside processing	438/782	156/331.7; 156/332	Moore; John C.
US 6867996 B2	20050315	Single-polarity programmable resistance-variable memory element	365/100	365/148; 365/163	Campbell; Kristy A. et al.
US 6867114 B2	20050315	Methods to form a memory cell with metal-rich metal chalcogenide	438/510	257/E27.004; 257/E45.002; 438/770	Moore; John T. et al.
US 6867064 B2	20050315	Method to alter chalcogenide glass for improved switching characteristics	438/95	438/102; 438/308; 438/795	Campbell; Kristy A. et al.

US 6864521	20050308	Method to control	257/296	257/4;	Moore;
B2	20030308	silver concentration	2311270	257/489;	John T. et
D2		in a resistance		257/508;	al.
		variable memory		257/750;	a1.
		element		257/751;	
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US 6861367 B2	20050301	Semiconductor processing method using photoresist and an antireflective coating	438/737	257/E21.029; 257/E21.232; 257/E21.577; 438/725; 438/736; 438/745	Gilton; Terry L. et al.
US 6858523 B2	20050222	Semiconductor processing methods of transferring patterns from patterned photoresists to materials, and structures comprising silicon nitride	438/585	257/E21.206; 257/E21.269; 438/595 CIPG 20060101 A H01L H01L21/02 L I R US M 20060101 CICL H01L CIPS H01L21/02 20060101 CIPG 20060101 A H01L H01L21/28 L I R US M 20060101 CICL H01L CIPS H01L21/28 L I R US M 20060101	DeBoer; Scott Jeffrey et al.
US 6857722 B1	20050222	Drop generating apparatus	347/40		Greiser; Christine M. et al.
US 6856943 B2	20050215	User perception tool	702/186	702/122; 702/187; 702/188; 709/224; 711/113; 717/106	Murphy; Stephen F et al.
US 6856323 B2	20050215	Layered image rendering	345/629	345/632; 345/633; 345/634; 345/639; 345/640	Moore; John S.
US 6856002 B2	20050215	Graded GexSe100-x concentration in	257/529	257/296; 257/528;	Moore; John T. et

		PCRAM		257/536; 257/55; 257/63;	al.
US 6833559 B2	20041221	Non-volatile resistance variable device	257/52	257/E45.002 257/245; 257/246; 257/29; 257/E29.101; 257/E29.17; 257/E45.002; 438/102; 438/292; 438/653; CIPG 20060101 A H01C H01C17/075 LIRUS M 20060101 CICL H01C CIPS H01C17/075 20060101 CIPG 20060101 A H01C H01C17/075 LIRUS M 20060101 CIPG 20060101 CIPG 20060101 CICL H01C CIPS H01C17/075 LIRUS M 20060101 CICL H01C CIPS H01C17/075 LIRUS M 20060101 CICL H01C CIPS H01C17/28 LIRUS M 20060101 CICL H01C CIPS; H01C17/28 20060101 CICL H01C CIPS; H01C17/28 20060101 CICL H01C CIPS; H01C17/28 20060101 CICL H01C CIPS;	Moore; John T.

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US 6833329	20041221	Methods of forming	438/770	257/E21.269;	Moore;
B1	ļ	oxide regions over		257/E21.625;	John T.
		semiconductor		438/176;	
		substrates		438/275;	
				438/762;	
				438/769;	+
				438/787	
US 6831019	20041214	Plasma etching	438/714	257/E21.241;	Li; Li et al.
B1		methods and methods		257/E21.268;	
		of forming memory		438/709;	
		devices comprising a		438/723;	
		chalcogenide		438/725;	
		comprising layer		438/743	
		received operably			
		proximate conductive			
		electrodes			
US 6829536	20041207	System and method	702/3	73/170.16	Moore;
B2		for processing			John S.
		weather information			
US 6823263	20041123	System and method	702/3		Kelly;
B1		for providing			Terence F.
		personalized weather			et al.
		reports and the like			
US 6818608	20041116		510/321	257/E21.255;	Moore;
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B2		dissolving compositions		510/224; 510/303; 510/374; 510/445; 510/499	John C.
US 6818481 B2	20041116	Method to manufacture a buried electrode PCRAM cell	438/130	257/E45.002; 438/768; 438/800; 438/95	Moore; John T. et al.
US 6815818 B2	20041109	Electrode structure for use in an integrated circuit	257/751	257/753; 257/762; 257/766; 257/774; 257/E21.582; 257/E23.02; 257/E27.004; 257/E45.002	Moore; John T. et al.
US 6815375 B2	20041109	Methods of forming dielectric materials and methods of processing semiconductor substrates	438/792	257/E21.193; 257/E21.268; 257/E21.293; 257/E29.165; 438/261; 438/769; 438/775; 438/791	Moore; John T.
US 6813178 B2	20041102	Chalcogenide glass constant current device, and its method of fabrication and operation	365/148	365/113; 365/45	Campbell; Kristy A. et al.
US 6812087 B2	20041102	Methods of forming non-volatile resistance variable devices and methods of forming silver selenide comprising structures	438/238	257/E45.002; 438/650; 438/672	Giltom; Terry L. et al.
US 6811096 B2	20041102	Spray gun with internal mixing structure	239/398	137/896; 239/407; 239/413	Frazier; Keith et al.
US 6806175 B2	20041019	Method for forming protective films and spacers	438/595	257/E21.507; 438/724; 438/744; 438/757; 438/791 CIPG	Moore; John T.

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US 6799830 B1	20041005	Drop generating apparatus	347/40		Brookfield; John M. et
					al.
US 6785357 B2	20040831	High energy X-ray mobile cargo inspection system with penumbra collimator	378/57	378/193; 378/196	Bernardi; Richard T. et al.
US 6784018 B2	20040831	Method of forming chalcogenide comprising devices and method of forming a programmable memory cell of memory circuitry	438/102	257/E45.002; 438/103; 438/308; 438/522; 438/537; 438/558; 438/84	Campbell; Kristy A. et al.
US 6780566 B2	20040824	High performance, photoimageable resin compositions and printing plates prepared therefrom	430/284.1	430/306; 522/95	Hu; Yuxin et al.
US 6777290 B2	20040817	Global column select structure for	438/257	438/405; 438/453	Moore; John T.

	T	accessing a memory			
US 6774418 B2	20040810	Low dielectric silicon oxynitride spacer films and devices incorporating such films	257/288	257/336; 257/344; 257/351; 257/411; 257/E21.268; 257/E21.269; 257/E21.507	Moore; John T.
US 6756634 B2	20040629	Gated semiconductor assemblies	257/324	257/410; 257/411; 257/E29.165; 257/E29.302	Helm; Mark A. et al.
US 6751114 B2	20040615	Method for programming a memory cell	365/100	365/185.24	Gilton; Terry L. et al.
US 6747327 B2	20040608	Transistor with nitrogen hardened gate oxide	257/410	257/411; 257/E21.193; 438/474; 438/761; 438/763	Moore; John T.
US 6744098 B2	20040601	Transistor devices	257/324	257/288; 257/325; 257/326; 257/E21.193; 257/E21.268; 257/E21.293; 257/E29.165	Moore; John T.
US 6737312 B2	20040518	Method of fabricating dual PCRAM cells sharing a common electrode	438/238	438/102; 438/381; 438/95	Moore; John
US 6734062 B2	20040511	Methods of forming DRAM cells	438/253	257/E21.65; 438/396	Gonzalez; Fernando et al.
US 6727192 B2	20040427	Methods of metal doping a chalcogenide material	438/795	257/E21.006; 257/E27.071; 257/E45.002	Moore; John T. et al.
US 6717115 B1	20040406	Semiconductor handler for rapid testing	219/444.1	118/724	Pfahnl; Andreas C. et al.
US 6713807 B2	20040330	Films doped with carbon for use in integrated circuit technology	257/306	257/900; 257/E21.274	Weimer; Ronald A. et al.
US 6711409 B1	20040323	Node belonging to multiple clusters in	455/445	370/242; 370/335;	Zavgren, Jr.; John R.

		an ad hoc wireless network		455/11.1; 455/13.1; 455/571	et al.
US 6710423 B2	20040323	Chalcogenide comprising device	257/528	257/E27.071; 257/E45.002	Moore; John T. et al.
US 6710173 B1	20040323	Stabilized viral envelope proteins and uses thereof	536/23.72	424/188.1; 424/208.1	Binley; James M. et al.
US 6709956 B2	20040323	Transistor and method of making the same	438/484	257/E21.193; 438/761; 438/763; 438/775	Moore; John T.
US 6709887 B2	20040323	Method of forming a chalcogenide comprising device	438/95	257/E21.006; 257/E27.071; 257/E45.002	Moore; John T. et al.
US 6707090 B2	20040316	DRAM cell constructions	257/296	257/401; 257/906; 257/E21.65	Gonzalez; Fernando et al.
US 6704033 B2	20040309	Goal-oriented design for the printer property's graphical user interface	715/777	715/715	Moore; John Anthony et al.
US 6699743 B2	20040302	Masked nitrogen enhanced gate oxide	438/216	257/E21.625; 438/275; 438/287; 438/591	Moore; John T. et al.
US 6696336 B2	20040224	Double sided container process used during the manufacture of a semiconductor device	438/253	257/E21.019; 257/E21.658; 438/254; 438/396; 438/397	DeBoer; Scott J. et al.
US 6693345 B2	20040217	Semiconductor wafer assemblies comprising photoresist over silicon nitride materials	257/640	257/629; 257/632; 257/639; 257/E21.257; 257/E21.259; 257/E21.293	Moore; John T. et al.
US 6690046 B2	20040210	Semiconductor assemblies, methods of forming structures over semiconductor substrates, and methods of forming transistors associated with semiconductor	257/288	257/401; 257/900	Beaman; Kevin L. et al.

		substrates		<u> </u>	<u> </u>
US 6686298 B1	20040203	Methods of forming structures over semiconductor substrates, and methods of forming transistors associated with semiconductor substrates	438/775	438/787	Beaman; Kevin L. et al.
US 6683984 B1	20040127	Digital imaging device with background training	382/190	382/199; 382/276; 382/278	Simske; Steven J et al.
US 6683935 B2	20040127	Computed tomography with virtual tilt and angulation	378/17		Moore; John F.
US 6682979 B2	20040127	Methods of forming transistors associated with semiconductor substrates	438/275	257/E21.269; 257/E21.625; 438/287; 438/591; 438/770; 438/775; 438/776	Moore; John T.
US 6677661 B1	20040113	Semiconductive wafer assemblies	257/649	257/640; 257/E21.029; 257/E21.206; 257/E21.257; 257/E21.293	DeBoer; Scott Jeffrey et al.
US 6674901 B1	20040106	Document analysis system and method	382/180	358/453; 382/282; 382/299	Simske; Steven J et al.
US 6670288 B1	20031230	layer of silicon nitride in a semiconductor fabrication process	438/791	257/E21.029; 257/E21.206; 257/E21.257; 257/E21.293; 438/483; 438/520	DeBoer; Scott Jeffrey et al.
US 6662186 B1	20031209	System and method for a data propagation file format	707/101	707/203; 715/511; 715/523; 717/122	Esquibel; Daniel M et al.
US 6660658 B2	20031209	Transistor structures, methods of incorporating nitrogen into siliconoxide-containing	438/775	257/E21.193; 257/E29.162; 438/776; 438/777	Sandhu; Gurtej S. et al.

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		of forming transistors			
US 6660657 B1	20031209	Methods of incorporating nitrogen into siliconoxide-containing	438/775	257/E21.193; 257/E29.162; 438/776; 438/777	Sandhu; Gurtej S. et al.
US 6654955 B1	20031125	Adding speech recognition libraries to an existing program at runtime	717/163	704/231; 704/275	Kusnitz; Jeffrey Alan et al.
US 6653184 B2	20031125	Method of forming transistors associated with semiconductor substrates comprising forming a nitrogencomprising region across an oxide region of a transistor gate	438/216	257/E21.269; 257/E21.625; 438/287; 438/591; 438/770; 438/776	Moore; John T.
US 6649543 B1	20031118	Methods of forming silicon nitride, methods of forming transistor devices, and transistor devices	438/792	257/288; 257/E21.193; 257/E21.268; 257/E21.293; 257/E29.165; 438/216; 438/261; 438/769; 438/775; 438/791	Moore; John T.
US 6645424 B2	20031111	Combustion synthesis of glass (Al2O3-CaO-X-Y) ceramic (TiB2) composites	264/649	264/234; 264/80; 501/32; 65/17.4; 65/17.5	Yi; Hu Chun et al.
US 6639243 B2	20031028	DRAM cell constructions	257/68	257/296; 257/347; 257/E21.65	Gonzalez; Fernando et al.
US 6638820 B2	20031028	Method of forming chalcogenide comprising devices, method of precluding diffusion of a metal into adjacent chalcogenide material, and	438/256	257/E29.101; 257/E29.17; 257/E45.002; 438/128; 438/130; 438/942; 438/953	Moore; John T.

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		chalcogenide			
US 6635530 B2	20031021	Methods of forming gated semiconductor assemblies	438/257	257/E29.165; 257/E29.302; 438/266; 438/268;	Helm; Mark A. et al.
US 6635043 B2	20031021	Container cap assembly having an enclosed penetrator	604/411	438/791 215/247; 215/316; 220/266; 604/415; 604/905	Daubert; Richard F. et al.
US 6631463 B1	20031007	Method and apparatus for patching problematic instructions in a microprocessor using software interrupts	712/227	712/244	Floyd; Michael Stephen et al.
US 6624088 B2	20030923	Method of forming low dielectric silicon oxynitride spacer films highly selective to etchants	438/756	257/E21.268; 257/E21.269; 257/E21.507; 438/789; 438/790; 438/794	Moore; John T.
US 6610041 B2	20030826	Penetrator for a container occluded by a stopper	604/415	141/329; 215/247; 604/411	Daubert; Richard F. et al.
US 6579664 B2	20030617	High performance, photoimageable resin compositions and printing plates prepared therefrom	430/284.1	430/18; 430/283.1; 430/285.1; 430/286.1; 430/287.1; 430/306; 522/100; 522/102; 522/103; 522/110; 522/95	Hu; Yuxin et al.
US D474731 S	20030520	Automobile console	D12/415		Moore; John A.
US 6551973 B1	20030422	Stable metal-safe stripper for removing cured negative-tone novolak and acrylic photoresists and post- etch residue	510/176	510/175; 510/255	Moore; John Cleaon

US 6548405 B2	20030415	Batch processing for semiconductor wafers to form aluminum nitride and titanium aluminum nitride	438/688	257/E21.029; 257/E21.035; 257/E21.168; 257/E21.17; 257/E21.292; 257/E21.576; 438/644; 438/660; 438/680	Kraus; Brenda D. et al.
US 6528396 B2	20030304	Transistor and method of making the same	438/484	257/E21.193; 438/761; 438/763; 438/775	Moore; John T.
US 6524295 B2	20030225	Container cap assembly having an enclosed penetrator	604/415	141/329; 215/247; 604/411	Daubert; Richard F. et al.
US 6518626 B1	20030211	Method of forming low dielectric silicon oxynitride spacer films highly selective of etchants	257/344	257/296; 257/336; 257/411; 257/E21.268; 257/E21.269; 257/E21.507	Moore; John T.
US 6515350 B1	20030204	Protective conformal silicon nitride films and spacers	257/640	257/649; 257/760; 257/900; 257/E21.507 CIPG 20060101 A H01L H01L21/02 L I R US M 20060101 CICL H01L CIPS H01L21/02 . 20060101 CIPG 20060101 A H01L H01L21/3205 L I R US M 20060101 CICL H01L CIPS H01L21/3205 L I R US M 20060101 CIPS H01L21/3205 20060101	Moore; John T.

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US D469241 S	20030128	Chaps	D2/860	D2/742	Moore; John
US 6498987 B1	20021224	System and method for providing personalized weather reports and the like	702/3		Kelly; Terence F. et al.
US 6481443 B1	20021119	Polish remover pad having protective rim	132/73	15/209.1; 401/8	Moore- Johnson; Misty et al.
US 6463420 B1	20021008	Online tracking of delivery status information over a computer network	705/28	705/26	Guidice; Rebecca R. et al.
US 6463122 B1	20021008	Mammography of computer tomography for imaging and therapy	378/65	378/17; 378/37; 378/64	Moore; John Fitzallen
US 6462402 B2	20021008	Microelectronic substrate comprised of etch stop layer, stiffening layer, and endpointing layer	257/635	257/634; 257/636; 257/637; 257/638; 257/E21.244	Moore; John T.
US 6462371 B1	20021008	Films doped with carbon for use in integrated circuit technology	257/306	257/309; 257/E21.274	Weimer; Ronald A. et al.
US 6461985 B1	20021008	Semiconductor wafer assemblies comprising silicon nitride, methods of forming silicon nitride, and methods of reducing stress on semiconductive wafers	438/791	257/E21.258; 257/E21.293; 257/E21.552; 438/624; 438/758	Moore; John T. et al.
US 6458663 B1	20021001	Masked nitrogen enhanced gate oxide	438/287	257/E21.625; 438/275; 438/591	Moore; John T. et al.
US 6440860 B1	20020827	Semiconductor processing methods of transferring patterns from	438/703	257/E21.206; 257/E21.269; 438/595; 438/724	DeBoer; Scott Jeffrey et al.

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		patterned photoresists		CIPG	
		to materials, and		20060101 A	
		structures comprising		H01L	
		silicon nitride		H01L21/02 L	
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				20060101	
US 6429151	20020806	Semiconductor wafer	438/791	257/610;	Moore;
B1		assemblies		257/635;	John T. et
		comprising silicon		257/E21.258;	al.
		nitride, methods of		257/E21.293;	
		forming silicon		257/E21.552;	
		nitride, and methods		438/441;	
		of reducing stress on		438/57;	
		semiconductive		438/638	
		wafers			
US 6429070	20020806	DRAM cell	438/253	257/E21.65;	Gonzalez;
B1		constructions, and		438/396	Fernando et
		methods of forming			al.
	,	DRAM cells			
US 6428072	20020806	Vehicle equipment	296/24.34	224/483;	Moore;
B1		console		296/37.12;	John A.
				296/37.8;	
				296/70	
US 6420268	20020716	Methods of forming	438/692	257/E21.244;	Moore;
B2		materials within		257/E21.55;	John T. et
		openings, and		438/700;	al.
		methods of forming	-	438/723;	
		isolation regions		438/724	
US 6417559	20020709	Semiconductor wafer	257/640	257/629;	Moore;
B1	-	assemblies		257/632;	John T. et
		comprising		257/639;	al.
		photoresist over		257/E21.257;	
		photoresist over		25 //E21.25 /;	

		.,.		0.57/201 050	
		silicon nitride		257/E21.259;	
		materials		257/E21.293	_
US 6391738	20020521	Semiconductor	438/402	257/E21.318;	Moore;
B1		processing method		257/E21.546;	John T.
		and trench isolation		438/143;	
		method		438/471;	
		memod		438/477	
TIC (201710	20020521) (d 1 CC '	420/252) (
US 6391710	20020521	Methods of forming	438/253	438/634;	Moore;
B1		capacitors		438/740;	John T. et
				438/970	al.
US 6385351	20020507	User interface high-	382/312	382/282;	Simske;
B1		lighter function to		382/311;	Steven J. et
		provide directed		382/319	al.
		input for image			
		processing			
110 626510	20020402		438/688	257/E21 020:	Kraus;
US 6365519	20020402	Batch processing for	438/088	257/E21.029;	
B2		semiconductor wafers		257/E21.035;	Brenda D.
		to form aluminum		257/E21.168;	et al.
		nitride and titanium		257/E21.17;	
		aluminum nitride		257/E21.292;	
				257/E21.576;	
				427/255.391;	
				438/660;	
i.				438/680	
110 (2(2105	20020226	N. C. Albard and	438/692	216/38;	Moore;
US 6362105	20020326	Method and	438/092	· ·	
B1		apparatus for		216/85;	John T.
		endpointing		216/88;	
		planarization of a		216/91;	
		microelectronic		257/E21.244;	
		substrate		438/745;	
				438/8	
US 6348380	20020219	Use of dilute steam	438/257	257/E21.209;	Weimer;
B1	20020213	ambient for	130/23/	257/E29.165;	Ronald A.
DI				438/593;	et al.
	ľ	improvement of flash			ct al.
		devices		438/594;	
				438/773	
US 6348365	20020219	PCRAM cell	438/130	257/E45.002;	Moore;
B1		manufacturing		438/466;	John T. et
				438/95	al.
US D453318	20020205	Automobile console	D12/415		Moore;
S					John A.
US 6342437	20020129	Transistor and	438/474	257/E21.193;	Moore;
	20020129		T T T T T T T T T T	438/761;	John T.
B1		method of making the		1	JOINI 1.
		same	# # # # # # # # # # # # # # # # # # #	438/763	D 1
US 6339747	20020115	Weather tracking and	702/3		Daly;
B1		display system and			Richard T.

		method			et al.
US 6335765 B1	20020101	Virtual presentation system and method	348/586	345/419; 345/629; 348/587; 348/598	Daly; Richard T. et al.
US 6328345 B1	20011211	Secondary tubing containment system for a metering pump	285/123.1	285/123.15; 285/13; 285/302; 285/343	Moore; John C. et al.
US 6326321 B1	20011204	Methods of forming a layer of silicon nitride in semiconductor fabrication processes	438/791	257/E21.029; 257/E21.206; 257/E21.257; 257/E21.293; 438/520; 438/775	DeBoer; Scott Jeffrey et al.
US 6323139 B1	20011127	Semiconductor processing methods of forming photoresist over silicon nitride materials	438/786	257/E21.257; 257/E21.259; 438/757; 438/769; 438/775; 438/787; 438/791	Moore; John T. et al.
US D450323 S	20011113	Printer properties graphical user interface computer icon for a display	D14/485		Moore; John Anthony et al.
US 6316372 B1	20011113	Methods of forming a layer of silicon nitride in a semiconductor fabrication process	438/791	257/E21.029; 257/E21.206; 257/E21.257; 257/E21.293; 438/520; 438/775	DeBoer; Scott Jeffrey et al.
US 6314433 B1	20011106	Frame-based heroic data recovery	707/202	360/53; 714/758	Mills; Mark E. et al.
US 6300671 B1	20011009	Semiconductor wafer assemblies comprising photoresist over silicon nitride materials	257/639	257/629; 257/632; 257/640; 257/E21.257; 257/E21.259	Moore; John T. et al.
US 6300253 B1	20011009	Semiconductor processing methods of forming photoresist over silicon nitride materials, and	438/763	257/E21.257; 257/E21.259; 438/757; 438/769; 438/778; 438/786;	Moore; John T. et al.

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		gaminan daasta		438/791	
		semiconductor wafer		430//71	
		assemblies			
		comprising			
		photoresist over			
		silicon nitride			
		materials			
US 6277081	20010821	Anesthetic gas	600/532	250/345	Susi; Roger
B1		detection apparatus			et al.
US 6274498	20010814	Methods of forming	438/692	257/E21.244;	Moore;
B1		materials within		257/E21.55;	John T. et
		openings, and method		438/700;	al.
		of forming isolation		438/723;	
		regions		438/724	
US 6271153	20010807	Semiconductor	438/787	257/E21.318;	Moore;
B1	20010007	processing method		257/E21.546;	John T.
51		and trench isolation		438/437;	
		method		438/763;	
· ·		method		438/783;	
				438/795	
TIC (2(2122	20010717	Courtains and mothed	382/311	430/193	Simske;
US 6263122	20010717	System and method	362/311		Steven J. et
B1		for manipulating			al.
		regions in a scanned			ai.
		image	100/550	0.57/201.000	
US 6251802	20010626	Methods of forming	438/778	257/E21.008;	Moore;
B1		carbon-containing		257/E21.27;	John T. et
		layers		438/623;	al.
				438/766;	
				438/780;	
				438/783;	
				438/924	
US 6234262	20010522	Snowmobile steering	180/182	180/186;	Moore;
B1	1	and suspension		180/190;	John W.
		system		280/93.51	
US 6230632	20010515	Selectively variable	108/180	211/194;	Moore;
B1	1	modular space		312/108;	John C.
	1	system with shelving		312/265.4	
	[and enclosures		1	
US 6218293	20010417	Batch processing for	438/644	257/E21.029;	Kraus;
B1		semiconductor wafers		257/E21.035;	Brenda D.
		to form aluminum		257/E21.168;	et al.
		nitride and titanium		257/E21.17;	
		aluminum nitride		257/E21.292;	
		arammam marac		257/E21.576	
US D440077	20010410	Combined newspaper	D6/466	237,221.373	Castillo;
S D440077	20010410	holder and storage	20,400		Earl J et al.
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		device	i	1	

US 6214697	20010410	Trench isolation for	438/424	257/E21.546;	Moore;
B1		semiconductor		438/296;	John T. et
		devices		438/435;	al.
				438/437;	
				438/761	
US 6200691	20010313	Oxidation resistance	428/615	428/627;	Moore;
B1		coating system for		428/641;	John J. et al.
		refractory metals		428/655;	
		·		428/663;	
				428/664	
US 6194321	20010227	Semiconductor	438/706	257/E21.029;	Moore;
B1		processing methods		257/E21.292;	John T. et
		utilizing boron and		438/708;	al.
		nitrogen, and		438/710;	
		semiconductor wafers		438/711;	
		comprising boron and		438/716;	
		nitrogen		438/717	
US 6188538	20010213	Retry off-track	360/77.04	369/53.37;	Mills; Mark
B1		positioning table		714/15;	E. et al.
				714/710	
US 6184571	20010206	Method and	257/635	257/915;	Moore;
B1		apparatus for		257/E21.244;	John T.
		endpointing		438/634	
		planarization of a			
		microelectronic			
		substrate			
US 6162737	20001219	Films doped with	438/738	257/437;	Weimer;
A		carbon for use in		257/E21.274;	Ronald A.
		integrated circuit		438/216;	et al.
	1	technology		438/784;	
				438/970	

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